2 AMPS SUFACE MOUNT GENERAL PUERPOSE SILLCON RECTIFIER

WG WildGoose

S2A-S2M

Features:

- ☐ Glass passivated device
- ☐ Ideal for surface mounted applications
- ☐ Low forward voltage drop
- ☐ Low reverse leakage

SOD-123FL

RoHS COMPLIANT





1.Cathode 2. Anode

Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	S2A	S2B	S2D	S2G	S2J	S2K	S2M	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T_c = 115 °C	$I_{F(AV)}$	2							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I_{FSM}	50							A
Maximum Instantaneous Forward Voltage at 2 A	V_F	1.1							V
Maximum DC Reverse Current T_a = 25 °C at Rated DC Blocking Voltage T_a =125 °C	I_R	5 50							μA
Typical Junction Capacitance (1)	C_j	25							pF
Typical Thermal Resistance (2)	$R_{\theta JA}$ $R_{\theta JC}$	75 22							°C/W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150							°C

(1) Measured at 1 MHz and applied reverse voltage of 4 V D.C
(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

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Typical Characteristics

Fig.1 Forward Current Derating Curve

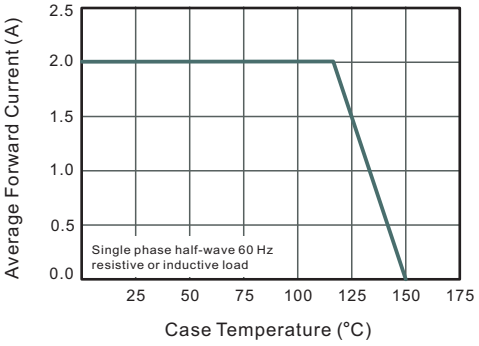


Fig.2 Typical Instaneous Reverse Characteristics

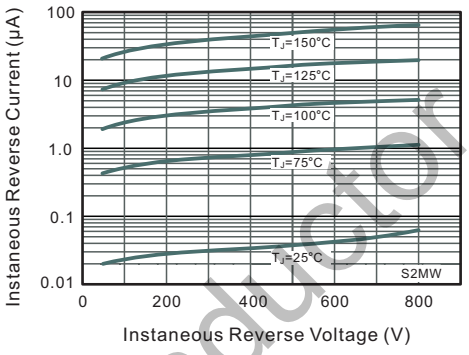


Fig.3 Typical Forward Characteristic

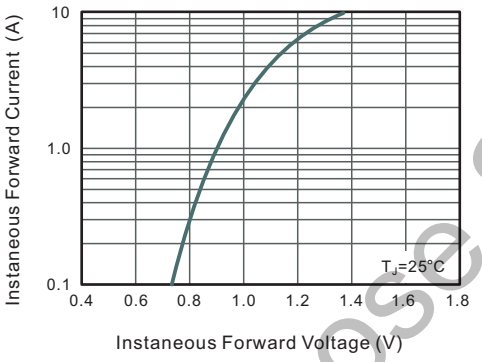


Fig.4 Typical Junction Capacitance

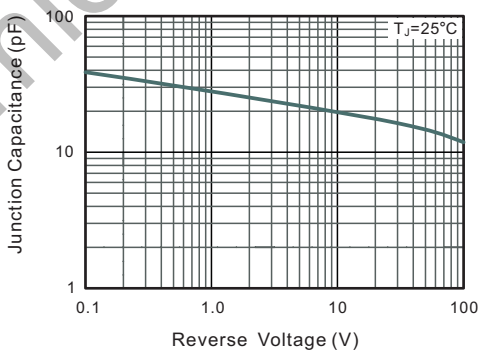
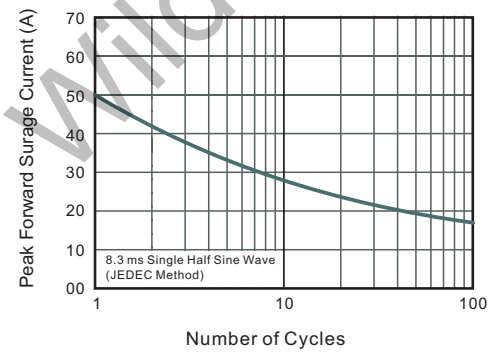


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current

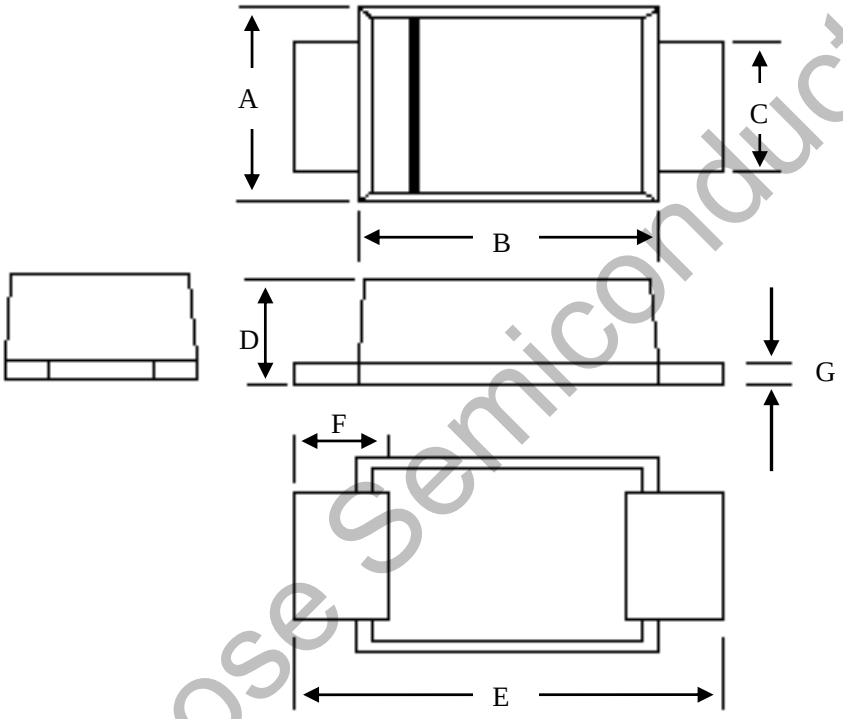


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Package Dimension

SOD-123FL

Unit: mm



DIM	MIN.	MAX.
A	1.70	1.90
B	2.70	2.90
C	0.80	1.10
D	0.95	1.10
E	3.50	3.70
F	0.45	0.90
G	0.10	0.30

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